

## LATERAL SEMICONDUCTOR STRUCTURE AND METHODS OF MANUFACTURE

**Patent number:** WO03036699  
**Publication date:** 2003-05-01  
**Inventor:** UDREA FLORIN (GB)  
**Applicant:** CAMBRIDGE SEMICONDUCTOR LTD (GB); UDREA FLORIN (GB)  
**Classification:**  
- **International:** H01L21/20; H01L27/12; H01L21/762; H01L21/04; H01L29/861; H01L29/78; H01L29/739; H01L21/84  
- **European:** H01L21/04D; H01L21/331G; H01L21/762D8; H01L21/84; H01L27/12B; H01L29/739C1; H01L29/78B1  
**Application number:** WO2002GB04738 20021021  
**Priority number(s):** US20010330506P 20011023

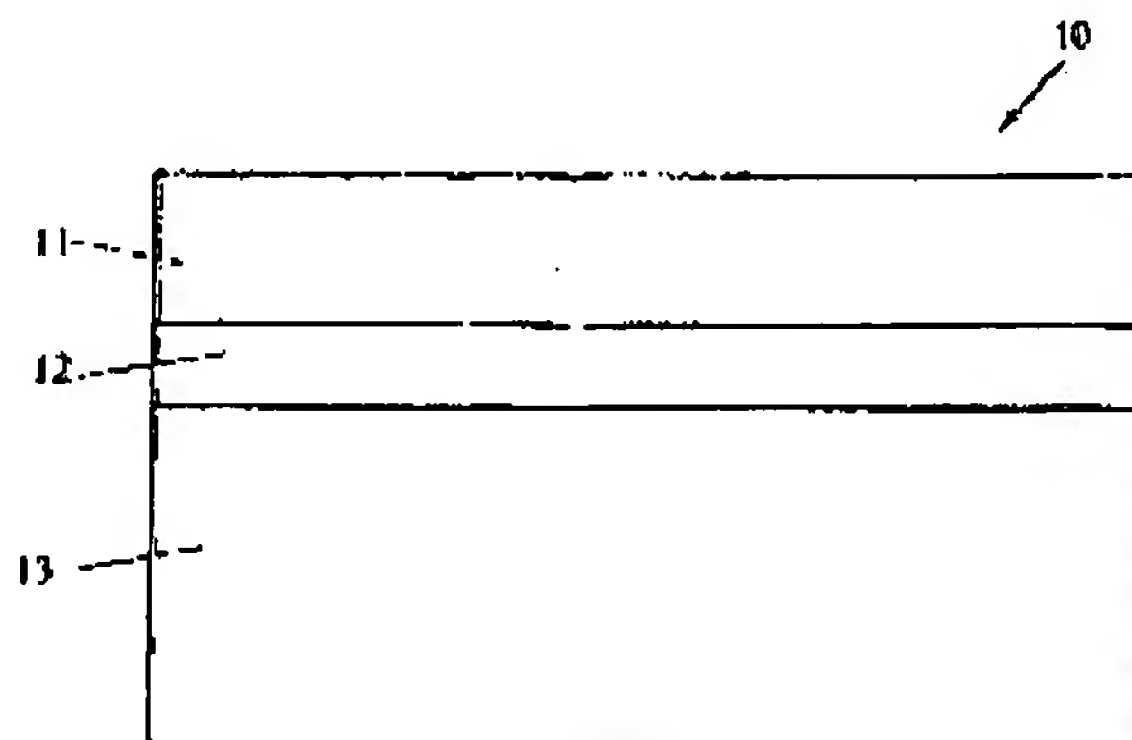
**Also published as:**  
WO03036699 (A3)

**Cited documents:**  
GB1114497  
EP1081748  
EP0905767  
US2001016399  
US6127243  
more >>

[Report a data error here](#)

### Abstract of WO03036699

A semiconductor structure (10) has a low bandgap semiconductor layer (11), a buried insulator layer (12) below the low bandgap semiconductor layer (11), and a wide bandgap semiconductor substrate (13). The low bandgap semiconductor layer (11) may be for example silicon, SiGe, GaAs or a heterojunction. The wide bandgap semiconductor layer (13) may be for example silicon carbide or diamond. A semiconductor device may be made by bonding a wide bandgap semiconductor wafer (13) via an insulator layer (12) to a low bandgap semiconductor wafer (11) and subsequently forming a semiconductor device in the low bandgap semiconductor wafer (11).



Data supplied from the esp@cenet database - Worldwide